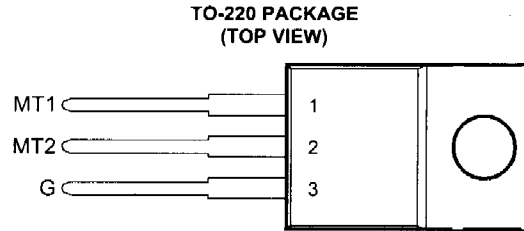


- Sensitive Gate Triacs
- 4 A RMS
- Glass Passivated Wafer
- 400 V to 800 V Off-State Voltage
- Max I_{GT} of 5 mA (Quadrants 1 - 3)



Pin 2 is in electrical contact with the mounting base

absolute maximum ratings over operating case temperature (unless otherwise noted)

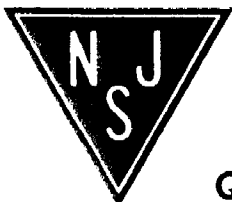
RATING		SYMBOL	VALUE	UNIT
Repetitive peak off-state voltage (see Note 1)	TIC206D	V_{DRM}	400	V
	TIC206M		600	
	TIC206S		700	
	TIC206N		800	
Full-cycle RMS on-state current at (or below) 85°C case temperature (see Note 2)		$I_{T(RMS)}$	4	A
Peak on-state surge current full-sine-wave (see Note 3)		I_{TSM}	25	A
Peak on-state surge current half-sine-wave (see Note 4)		I_{TSM}	30	A
Peak gate current		I_{GM}	±0.2	A
Peak gate power dissipation at (or below) 85°C case temperature (pulse width ≤ 200 μs)		P_{GM}	1.3	W
Average gate power dissipation at (or below) 85°C case temperature (see Note 5)		$P_{G(AV)}$	0.3	W
Operating case temperature range		T_C	-40 to +110	°C
Storage temperature range		T_{stg}	-40 to +125	°C
Lead temperature 1.6 mm from case for 10 seconds		T_L	230	°C

- NOTES: 1. These values apply bidirectionally for any value of resistance between the gate and Main Terminal 1.
 2. This value applies for 50-Hz full-sine-wave operation with resistive load. Above 85°C derate linearly to 110°C case temperature at the rate of 160 mA/°C.
 3. This value applies for one 50-Hz full-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
 4. This value applies for one 50-Hz half-sine-wave when the device is operating at (or below) the rated value of on-state current. Surge may be repeated after the device has returned to original thermal equilibrium. During the surge, gate control may be lost.
 5. This value applies for a maximum averaging time of 20 ms.

electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS			MIN	TYP	MAX	UNIT
I_{DRM} Repetitive peak off-state current	$V_D = \text{rated } V_{DRM}$	$I_G = 0$	$T_C = 110^\circ\text{C}$			±1	mA
I_{GTM} Peak gate trigger current	$V_{supply} = +12\text{ V}\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		0.5	5	mA
	$V_{supply} = +12\text{ V}\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		-1.5	-5	
	$V_{supply} = -12\text{ V}\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		-2	-5	
	$V_{supply} = -12\text{ V}\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		3.6	10	
V_{GTM} Peak gate trigger voltage	$V_{supply} = +12\text{ V}\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		0.7	2	V
	$V_{supply} = +12\text{ V}\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		-0.7	-2	
	$V_{supply} = -12\text{ V}\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		-0.8	-2	
	$V_{supply} = -12\text{ V}\dagger$	$R_L = 10\ \Omega$	$t_{p(g)} > 20\ \mu\text{s}$		0.8	2	

† All voltages are with respect to Main Terminal 1.



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TIC206 SERIES SILICON TRIACS

electrical characteristics at 25°C case temperature (unless otherwise noted) (continued)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{TM} Peak on-state voltage	$I_{TM} = \pm 4.2$ A $I_G = 50$ mA (see Note 6)		± 1.3	± 2.2	V
I_H Holding current	$V_{supply} = +12$ V† $I_G = 0$ Init' $I_{TM} = 100$ mA $V_{supply} = -12$ V† $I_G = 0$ Init' $I_{TM} = -100$ mA		2 -4	15 -15	mA
I_L Latching current	$V_{supply} = +12$ V† $V_{supply} = -12$ V† (see Note 7)			30 -30	mA
dv/dt Critical rate of rise of off-state voltage	$V_{DRM} = \text{Rated } V_{DRM}$ $I_G = 0$ $T_C = 110^\circ\text{C}$		± 50		V/ μs
dv/dt _(c) Critical rise of commutation voltage	$V_{DRM} = \text{Rated } V_{DRM}$ $I_{TRM} = \pm 4.2$ A $T_C = 85^\circ\text{C}$	± 1	± 1.3	± 2.5	V/ μs

† All voltages are with respect to Main Terminal 1.

NOTES: 6. This parameter must be measured using pulse techniques, $t_p \leq 1$ ms, duty cycle $\leq 2\%$. Voltage-sensing contacts separate from the current carrying contacts are located within 3.2 mm from the device body.

7. The triacs are triggered by a 15-V (open circuit amplitude) pulse supplied by a generator with the following characteristics:
 $R_G = 100 \Omega$, $t_{p(g)} = 20 \mu\text{s}$, $t_r \leq 15$ ns, $f = 1$ kHz.

thermal characteristics

PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$ Junction to case thermal resistance			7.8	$^\circ\text{C/W}$
$R_{\theta JA}$ Junction to free air thermal resistance			62.5	$^\circ\text{C/W}$

TYPICAL CHARACTERISTICS

